



DMT3020LFVW

### **Product Summary**

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub> Max       | I <sub>D</sub> Max<br>T <sub>C</sub> = +25°C |  |  |
|-------------------|-------------------------------|--|--|--|
| 30V               | $17m\Omega @ V_{GS} = 10V$    | - 38A  |  |  |
| 307               | 28mΩ @ V <sub>GS</sub> = 4.5V | 30A  |  |  |

### Description

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$ , yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- Power Management Functions
- Analog Switch

#### PowerDI3333-8 (SWP) (Type UX)

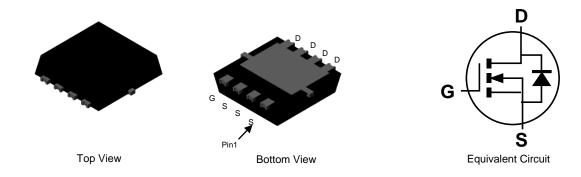
#### 30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (SWP) (Type UX)

#### Features

- Low R<sub>DS(ON)</sub> Ensures On State Losses Are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

## **Mechanical Data**

- Case: PowerDl<sup>®</sup>3333-8 (SWP) (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.03 grams (Approximate)



## Ordering Information (Note 4)

|        | Part Number  | Case                          | Packaging        |  |  |  |
|--------|--|-------------------------------|------------------|--|--|--|
|        | DMT3020LFVW-7  | PowerDI3333-8 (SWP) (Type UX) | 2000/Tape & Reel |  |  |  |
|        | DMT3020LFVW-13   | PowerDI3333-8 (SWP) (Type UX) | 3000/Tape & Reel |  |  |  |
| Notes: | Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. |                               |                  |  |  |  |

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See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



 $\begin{array}{l} \underline{AT3} = \mbox{Product Type Marking Code} \\ \hline \underline{YY} WW = \mbox{Date Code Marking} \\ \hline \underline{YY} = \mbox{Last Two Digits of Year (ex: 18 = 2018)} \\ WW = \mbox{Week Code (01 to 53)} \end{array}$ 



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic   |                 |  | Symbol           | Value    | Unit |
|--|-----------------|--|------------------|----------|------|
| Drain-Source Voltage   |                 |  | V <sub>DSS</sub> | 30       | V    |
| Gate-Source Voltage  |                 |  | V <sub>GSS</sub> | ±20      | V    |
| Continuous Drain Current, $V_{GS}$ = 10V (Note 7)                      | Steady<br>State | T <sub>C</sub> = +25°C<br>T <sub>C</sub> = +70°C | ID               | 38<br>30 | А    |
| Maximum Body Diode Forward Current (Note 7)                            |                 |  | Is               | 30       | А    |
| Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)                    |                 |  | I <sub>DM</sub>  | 40       | А    |
| Pulsed Drain Body Diode Forward Current (380µs Pulse, Duty Cycle = 1%) |                 |  | I <sub>SM</sub>  | 40       | А    |
| Avalanche Current (L = 0.1mH) (Note 8)                                 |                 |  | IAS              | 13       | А    |
| Avalanche Energy (L = 0.1mH) (Note 8)                                  |                 |  | E <sub>AS</sub>  | 8.5      | mJ   |

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic  | Symbol           | Value           | Unit        |      |
|---|------------------|-----------------|-------------|------|
| Total Power Dissipation (Note 5)                              |                  | PD              | 1.0         | W    |
| Thermal Resistance, Junction to Ambient (Note 5)              | Steady State     | $R_{	heta JA}$  | 124         | °C/W |
| Total Power Dissipation (Note 6)                              |                  | PD              | 2.0         | W    |
| Thermal Resistance, Junction to Ambient (Note 6) Steady State |                  | $R_{\theta JA}$ | 62          | °C/W |
| Thermal Resistance, Junction to Case (Note 7)                 | R <sub>0JC</sub> | 4.0             | C/W         |      |
| Operating and Storage Temperature Range                       |                  | TJ, TSTG        | -55 to +150 | °C   |

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

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|--|---------------------|--------|----------|------|-------|--|--|
|  | Symbol              | Min    | Тур      | Max  | Unit  | Test Condition   |  |
| OFF CHARACTERISTICS (Note 8)                         | 514                 |        |          | r    |       |  |  |
| Drain-Source Breakdown Voltage                       | BV <sub>DSS</sub>   | 30.0   | —        | _    | V     | $V_{GS} = 0V, I_D = 250\mu A$                              |  |
| Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$ | I <sub>DSS</sub>    | —      |          | 1.0  | μA    | $V_{DS} = 24V, V_{GS} = 0V$                                |  |
| Gate-Source Leakage                                  | I <sub>GSS</sub>    | _      | _        | ±100 | nA    | $V_{GS} = \pm 20V, V_{DS} = 0V$                            |  |
| ON CHARACTERISTICS (Note 8)                          |                     |        |          |      |       |  |  |
| Gate Threshold Voltage                               | V <sub>GS(TH)</sub> | 1.0    | —        | 2.5  | V     | $V_{DS} = V_{GS}$ , $I_D = 250 \mu A$                      |  |
| Static Drain-Source On-Resistance                    |                     |        | 12.5     | 17   | mΩ    | $V_{GS} = 10V, I_D = 9.0A$                                 |  |
| Static Drain-Source On-Resistance                    | R <sub>DS(ON)</sub> | _      | 20.5     | 28   | 11122 | $V_{GS} = 4.5V, I_D = 7.0A$                                |  |
| Diode Forward Voltage                                | V <sub>SD</sub>     | Ι      | 0.8      | 1.2  | V     | $V_{GS} = 0V, I_S = 2A$                                    |  |
| DYNAMIC CHARACTERISTICS (Note 9)                     |                     |        |          |      |       | -  |  |
| Input Capacitance                                    | Ciss                | —      | 393      | —    | pF    |  |  |
| Output Capacitance                                   | Coss                | _      | 173      | —    | pF    | V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V,<br>f = 1.0MHz |  |
| Reverse Transfer Capacitance                         | C <sub>rss</sub>    | Ι      | 27       | _    | pF    | 1 = 1.00012  |  |
| Gate Resistance                                      | Rg                  |        | 1.1      | —    | Ω     | $V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$                     |  |
| Total Gate Charge (V <sub>GS</sub> = 10V)            | Qg                  | Ι      | 7.0      | —    | nC    |  |  |
| Total Gate Charge (V <sub>GS</sub> = 4.5V)           | Qg                  | _      | 3.6      | _    | nC    |  |  |
| Gate-Source Charge                                   | Q <sub>gs</sub>     |        | 0.9      | —    | nC    | V <sub>DD</sub> = 15V, I <sub>D</sub> = 9A                 |  |
| Gate-Drain Charge                                    | Q <sub>gd</sub>     | Ι      | 1.5      | —    | nC    |  |  |
| Turn-On Delay Time                                   | t <sub>D(ON)</sub>  | _      | 1.8      | _    | ns    | <br>V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V,          |  |
| Turn-On Rise Time                                    | t <sub>R</sub>      | Ι      | 1.9      | —    | ns    |  |  |
| Turn-Off Delay Time                                  | t <sub>D(OFF)</sub> | —      | 7.5      | —    | ns    | $R_G = 6\Omega, I_D = 9A$                                  |  |
| Turn-Off Fall Time                                   | tF                  | _      | 2.4      | _    | ns    |  |  |
| Reverse Recovery Time                                | t <sub>RR</sub>     | —      | 10       | —    | ns    |  |  |
| Reverse Recovery Charge                              | Q <sub>RR</sub>     | -      | 2.6      | _    | nC    | I <sub>F</sub> = 9A, dl/dt = 100A/µs                       |  |

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

7.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ .

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.



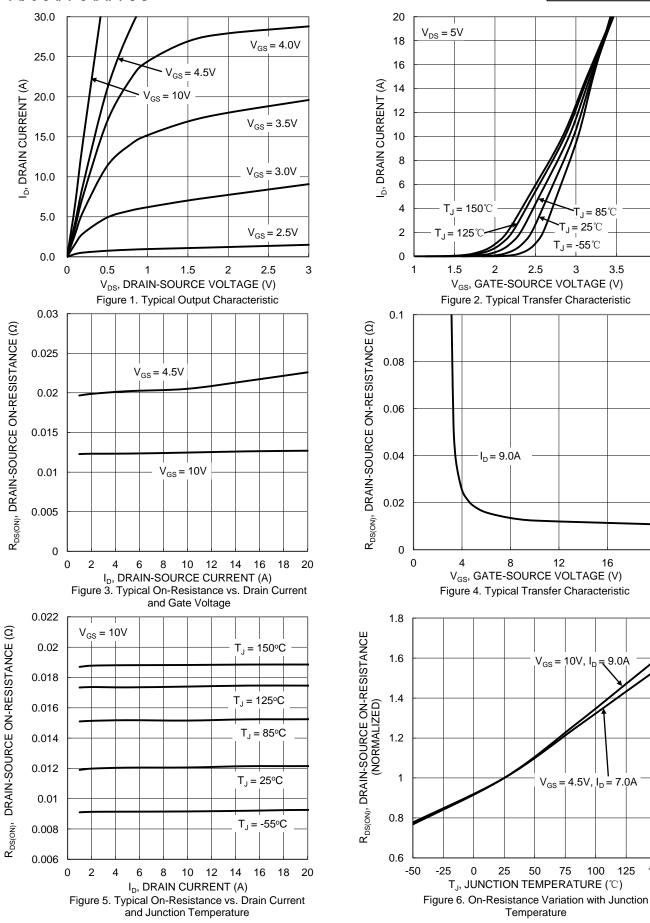


3.5

16

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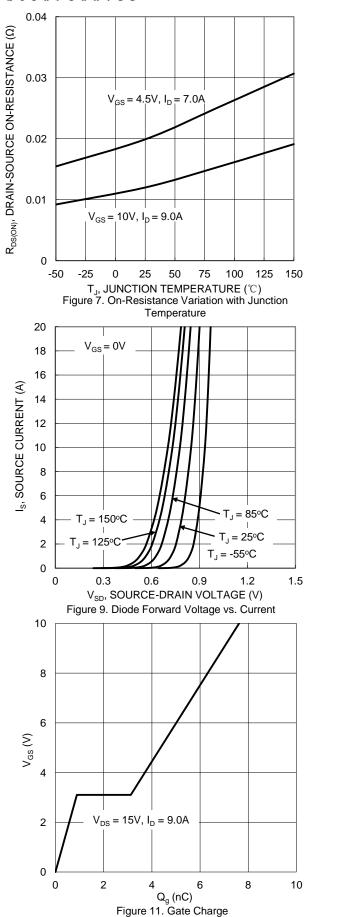
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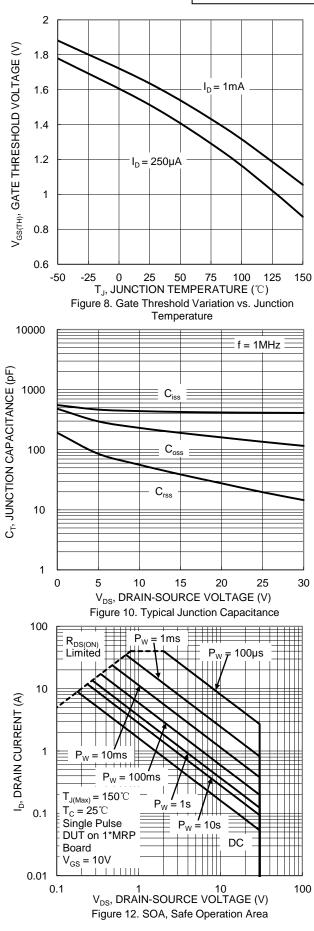


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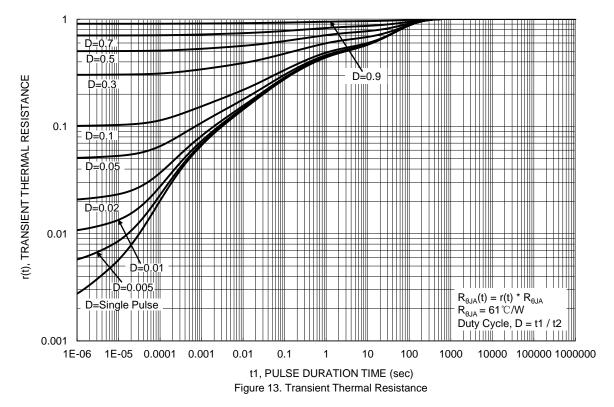






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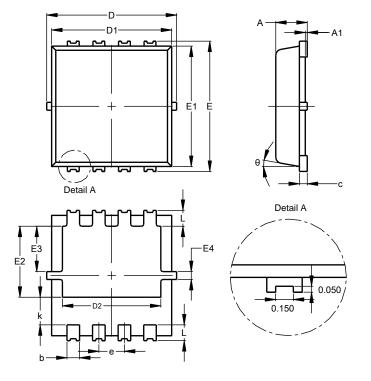




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (SWP) (Type UX)

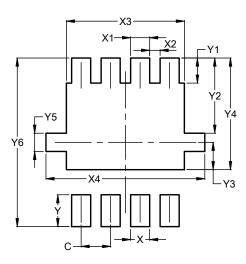


| PowerDI3333-8 (SWP) |                      |            |      |  |  |  |
|---------------------|----------------------|------------|------|--|--|--|
| (Type UX)           |                      |            |      |  |  |  |
| Dim                 |                      | Min Max Ty |      |  |  |  |
| Α                   | 0.75                 | 0.85       | 0.80 |  |  |  |
| A1                  | 0.00                 | 0.05       |      |  |  |  |
| b                   | 0.25                 | 0.40       | 0.32 |  |  |  |
| c                   | 0.10                 | 0.25       | 0.15 |  |  |  |
| D                   | 3.20                 | 3.40       | 3.30 |  |  |  |
| D1                  | 2.95                 | 3.15       | 3.05 |  |  |  |
| D2                  | 2.30                 | 2.70       | 2.50 |  |  |  |
| Е                   | 3.20                 | 3.40       | 3.30 |  |  |  |
| E1                  | 2.95                 | 3.15       | 3.05 |  |  |  |
| E2                  | 1.60                 | 2.00       | 1.80 |  |  |  |
| E3                  | 0.95                 | 1.35       | 1.15 |  |  |  |
| E4                  | 0.10                 | 0.30       | 0.20 |  |  |  |
| е                   | _                    | _          | 0.65 |  |  |  |
| k                   | 0.50                 | 0.90       | 0.70 |  |  |  |
| L                   | 0.30                 | 0.50       | 0.40 |  |  |  |
| θ                   | 0°                   | 12°        | 10°  |  |  |  |
| All [               | All Dimensions in mm |            |      |  |  |  |

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (SWP) (Type UX)



| Dimensions | Value (in mm) |
|------------|---------------|
| С          | 0.650         |
| Х          | 0.420         |
| X1         | 0.420         |
| X2         | 0.230         |
| X3         | 2.600         |
| X4         | 3.500         |
| Y          | 0.700         |
| Y1         | 0.550         |
| Y2         | 1.650         |
| Y3         | 0.600         |
| Y4         | 2.450         |
| Y5         | 0.400         |
| Y6         | 3.700         |



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